



EMH2407 — N-Channel Silicon MOSFET

General-Purpose Switching Device Applications

Features

- Low ON-resistance.
- Best suited for LiB charging and discharging switch.
- Common-drain type.
- 2.5V drive.

Specifications

Absolute Maximum Ratings at $T_a=25^\circ\text{C}$

Parameter	Symbol	Conditions	Ratings	Unit
Drain-to-Source Voltage	V_{DSS}		20	V
Gate-to-Source Voltage	V_{GSS}		± 12	V
Drain Current (DC)	I_D		6	A
Drain Current (Pulse)	I_{DP}	$PW \leq 10\mu\text{s}$, duty cycle $\leq 1\%$	40	A
Allowable Power Dissipation	P_D	When mounted on ceramic substrate (900mm ² X0.8mm) 1unit	1.3	W
Total Dissipation	P_T	When mounted on ceramic substrate (900mm ² X0.8mm)	1.4	W
Channel Temperature	T_{ch}		150	$^\circ\text{C}$
Storage Temperature	T_{stg}		-55 to +150	$^\circ\text{C}$

Electrical Characteristics at $T_a=25^\circ\text{C}$

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Drain-to-Source Breakdown Voltage	$V_{(BR)DSS}$	$I_D=1\text{mA}$, $V_{GS}=0\text{V}$	20			V
Zero-Gate Voltage Drain Current	I_{DSS}	$V_{DS}=20\text{V}$, $V_{GS}=0\text{V}$			1	μA
Gate-to-Source Leakage Current	I_{GSS}	$V_{GS}=\pm 8\text{V}$, $V_{DS}=0\text{V}$			± 10	μA
Cutoff Voltage	$V_{GS(off)}$	$V_{DS}=10\text{V}$, $I_D=1\text{mA}$	0.5		1.3	V
Forward Transfer Admittance	$ y_{fs} $	$V_{DS}=10\text{V}$, $I_D=3\text{A}$	3	5		S

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EMH2407

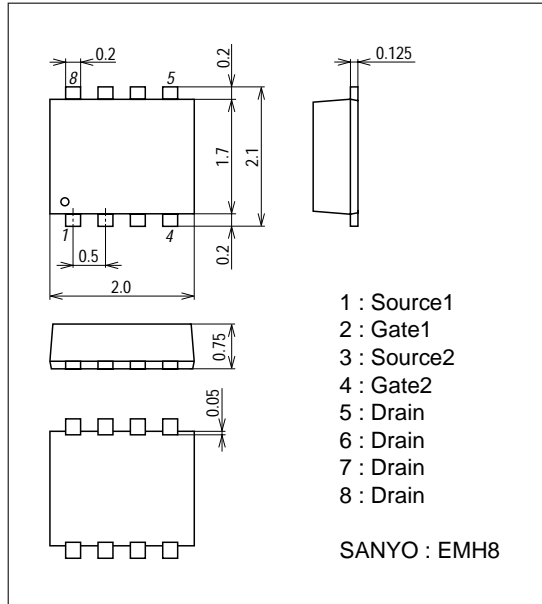
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Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Static Drain-to-Source On-State Resistance	$R_{DS(on)1}$	$I_D=3A, V_{GS}=4.5V$	13	19	25	$m\Omega$
	$R_{DS(on)2}$	$I_D=3A, V_{GS}=4V$	14	20	26	$m\Omega$
	$R_{DS(on)3}$	$I_D=1.5A, V_{GS}=2.5V$	16	28	39	$m\Omega$
Input Capacitance	C_{iss}	$V_{DS}=10V, f=1MHz$		580		pF
Output Capacitance	C_{oss}	$V_{DS}=10V, f=1MHz$		95		pF
Reverse Transfer Capacitance	C_{rss}	$V_{DS}=10V, f=1MHz$		75		pF
Turn-ON Delay Time	$t_{d(on)}$	See specified Test Circuit.		310		ns
Rise Time	t_r	See specified Test Circuit.		1020		ns
Turn-OFF Delay Time	$t_{d(off)}$	See specified Test Circuit.		3000		ns
Fall Time	t_f	See specified Test Circuit.		2250		ns
Total Gate Charge	Q_g	$V_{DS}=10V, V_{GS}=4.5V, I_D=6A$		6.3		nC
Gate-to-Source Charge	Q_{gs}	$V_{DS}=10V, V_{GS}=4.5V, I_D=6A$		0.83		nC
Gate-to-Drain "Miller" Charge	Q_{gd}	$V_{DS}=10V, V_{GS}=4.5V, I_D=6A$		1.9		nC
Diode Forward Voltage	V_{SD}	$I_S=6A, V_{GS}=0V$		0.78	1.2	V

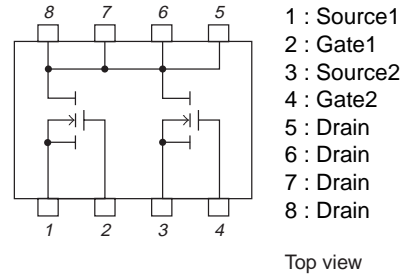
Package Dimensions

unit : mm (typ)

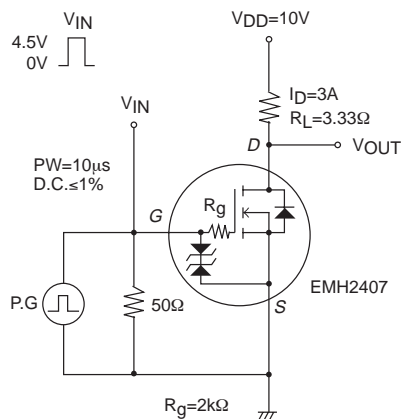
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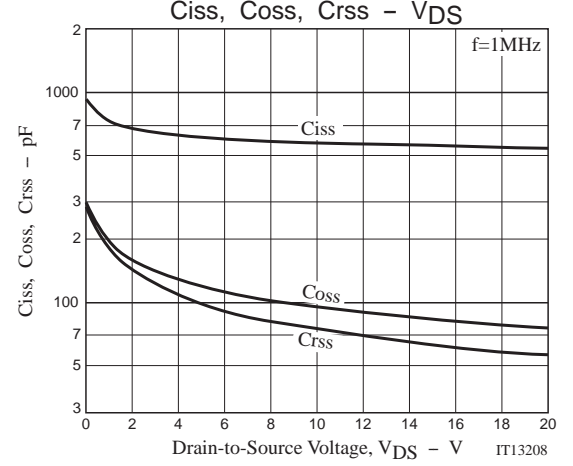
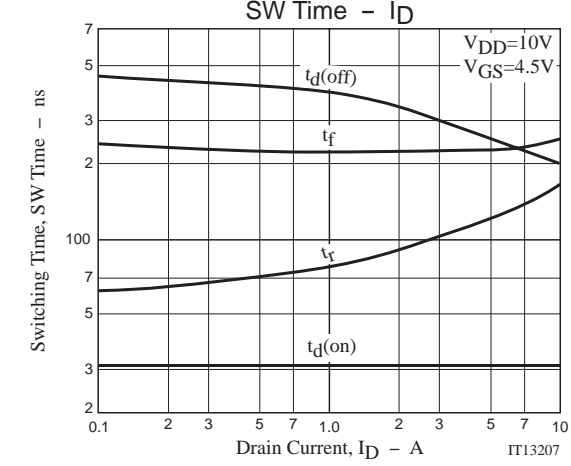
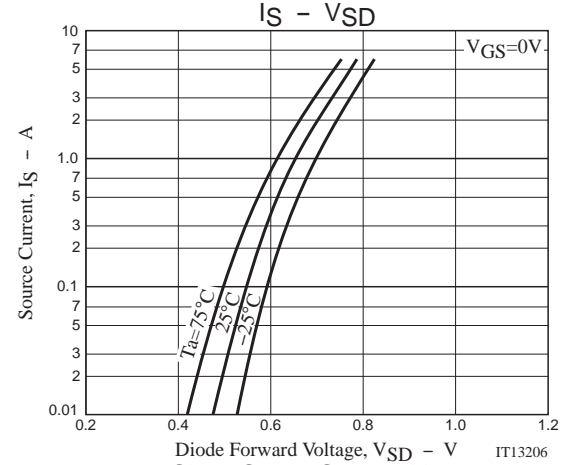
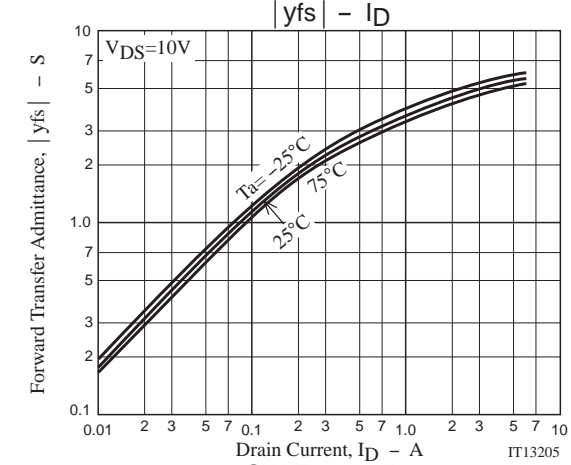
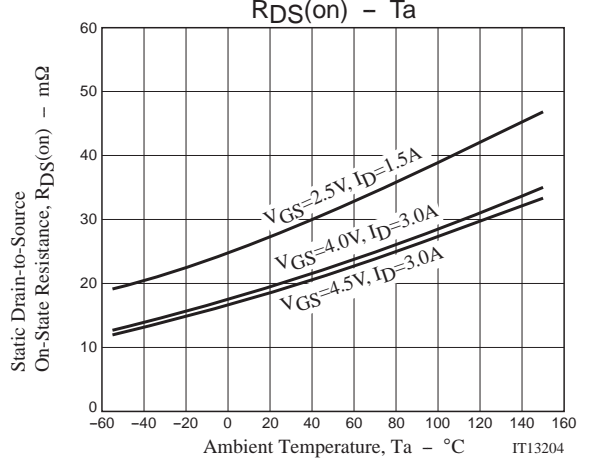
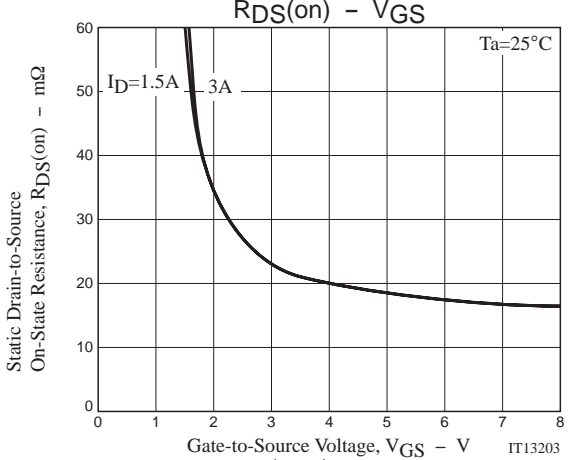
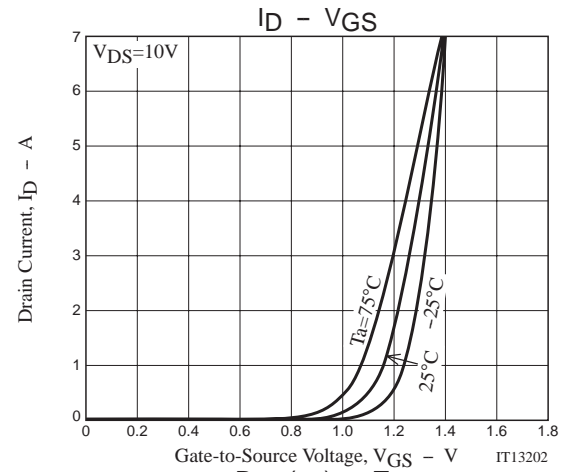
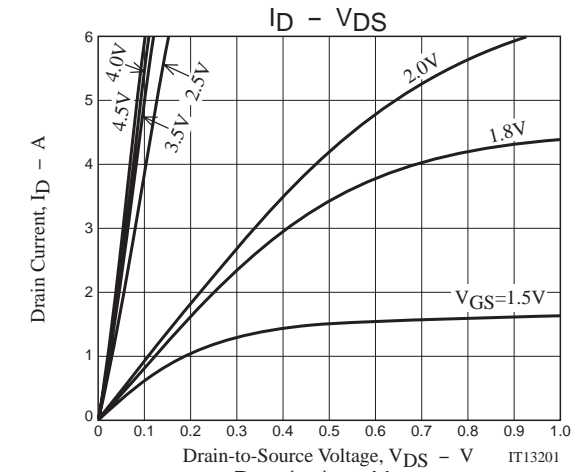


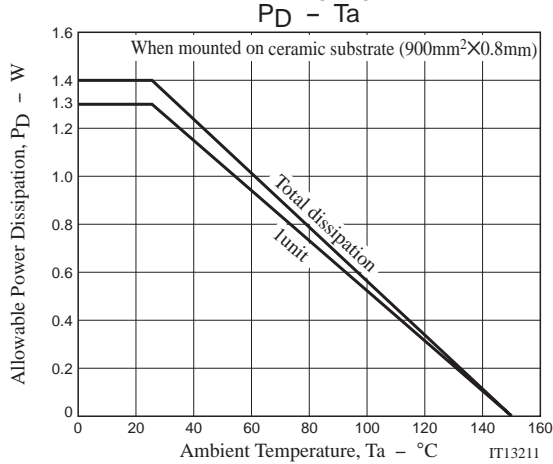
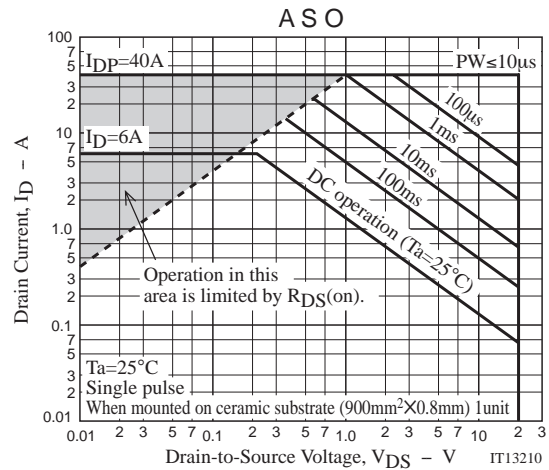
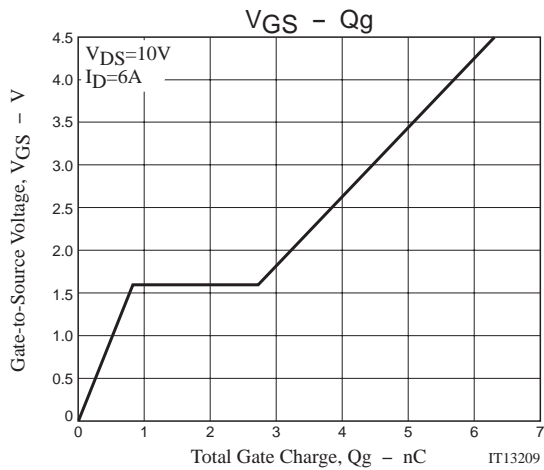
Electrical Connection



Switching Time Test Circuit







Note on usage : Since the EMH2407 is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.ged objects.ged objects.

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